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Magnetism and Faraday Rotation in Oxygen-Deficient Polycrystalline and Single-Crystal Iron-Substituted Strontium Titanate

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ABSTRACT

Both polycrystalline and single-crystal films of iron-substituted strontium titanate, $\text{Sr}(\text{Ti}_{0.65}\text{Fe}_{0.35})\text{O}_{3-\delta}$, prepared by pulsed laser deposition (PLD), show room temperature magnetism and Faraday rotation (FR), with the polycrystalline films exhibiting higher saturation magnetization and FR. The magnetic properties vary with the oxygen pressure at which the films are grown, showing a maximum at pressures of ~ 4 μTorr at which the unit cell volume is largest. The results are discussed in terms of the oxygen stoichiometry and corresponding Fe valence states, the structure and strain state, and the presence of small volume fractions of metallic Fe in single-crystal films grown at the optimum deposition pressure. Integration of magneto-optical polycrystalline films on an optical waveguide device demonstrates a nonreciprocal phase shift.

I. INTRODUCTION

Complex oxides exhibit a wide range of useful properties such as high temperature superconductivity, ferroelectricity, colossal magnetoresistance, magnetism, magneto-electricity, magneto-optical activity, and multiferroicity that have inspired spintronic, magnetoelectronic, and optical applications [1-6]. Transition-metal-substituted perovskites or perovskite-derived structures are particularly interesting because their properties can be tuned by cation substitution over extensive composition ranges, and because they can be epitaxially grown on a buffered Si substrate [7-10]. Beyond cation composition, the properties are also very sensitive to the growth conditions and substrate used, which affect the microstructure, film strain [7], oxygen deficiency, the cation valence states, and the ordering of cations within the A and B sites.

Iron-substituted strontium titanate or $\text{SrTi}_{1-x}\text{Fe}_x\text{O}_{3-\delta}$ (STF) (here δ represents the oxygen deficiency with respect to a stoichiometric perovskite $\text{SrTi}_{1-x}\text{Fe}_x\text{O}_3$, i.e., one in which the Fe is present as Fe^{4+}) has been extensively characterized as a mixed electronic-ionic conductor [11-15] and for its magnetic, magneto-optical, ferroelectric, and catalytic properties [16-19]. Characterization of STF has included determining its oxygen content via thermogravimetric analysis and coulometric titration [20,21], and measurements of ionic/electronic conductivity and impedance [12,13,15,22-24]. The magnetic properties are believed to be related to oxygen vacancies [16,20,25], although the origin of the magnetism is not fully understood. We have previously found that epitaxial STF and $\text{Sr}(\text{Ti}_{1-x}\text{Co}_x)\text{O}_{3-\delta}$ (STCo) films on SrTiO_3 (STO), LaAlO_3 , and $\text{CeO}_2/\text{yttria-stabilized zirconia}$ (YSZ)-buffered (001) Si substrates grown in vacuum with $x = 0.1$ to 0.5 , i.e. non-dilute systems, exhibited room-temperature magnetism and anisotropy with an out-of-plane magnetic easy axis that was attributed to magnetoelastic effects [16,17,26-28]. However, films deposited in oxygen had no significant room-temperature magnetism. The magnetic moment of vacuum-deposited epitaxial STF films persisted to a tempera-

ture of $>1000^\circ\text{C}$ and the magnetization decreased slowly as a function of temperature [16,29,30]. Depending on the thickness and deposition conditions, STF could be grown as a single crystal film on STO, or as a double epitaxial film consisting of an (001)-oriented STF film with (011)-oriented crystals growing within it, both orientations being epitaxial with the substrate [31]. The single crystal and double epitaxial microstructures differed in their strain state, uniformity of the Fe distribution, and magnetic properties [19,31].

These experimental results led to the conclusion that strain and oxygen stoichiometry were key structural factors in determining the magnetic properties of the STF and STCo films (factors that are also important in many other oxide systems [29,32],) but there are few reports on the effect of oxygen pressure during growth [33,34], and polycrystalline films have not been investigated. We report on the correlations among the microstructure, valence, and distribution of the Fe ions as well as the room temperature magnetic properties of STF films as a function of base pressure P , characterized by high-resolution x-ray diffraction (XRD), transmission electron microscopy (TEM), Faraday rotation (FR), magnetometry, and Mössbauer spectroscopy. The STF films on Si were polycrystalline but exhibited a magnetic moment and FR up to 65% higher than the single-crystal film deposited on an STO substrate. From the viewpoint of applications, the formation of polycrystalline magnetic perovskite films on silica or other non-epitaxial substrates allows the useful properties of STF to be easily introduced into complementary metal-oxide semiconductor (CMOS) devices and into optical devices such as isolators and magnetophotonic crystals [4,35-39], spatial light modulators [40-42], or magneto-optical holographic memories [43-46]. First-principles calculations demonstrate the importance of oxygen defects and exchange interactions in determining the magnetic properties.

II. FILM GROWTH AND CHARACTERIZATION

A. Film preparation

In this work, STF films were fabricated on silicon covered by a native oxide and on STO substrates under various P using pulsed laser deposition (PLD). The $\text{SrTi}_{0.62}\text{Fe}_{0.38}\text{O}_{3-\delta}$ target was prepared using a conventional mixed oxide sintering method [47]. During film deposition, the KrF excimer laser (wavelength $\lambda = 248$ nm) was pulsed at a frequency of 10 Hz with a pulse duration of 25 ns. The spot size on the target was $0.5 \text{ mm} \times 2.0 \text{ mm}$, and the energy density at the target surface was $\sim 1.3 \text{ J cm}^{-2}$ during the pulse. The deposition rate was $1.8\text{--}2.7 \text{ nm min}^{-1}$. STF films of thickness $70 \pm 10 \text{ nm}$ were deposited by PLD onto 0.38-mm-thick double-side-polished (001) Si substrates and onto 0.5-mm-thick double-side-polished (001) STO substrates. Films were grown simultaneously on both substrate types in each deposition run. The substrates were placed 80 mm from the target, and the substrate holder was heated to 650°C and was rotated for uniform growth. This temperature was chosen to minimize the formation of secondary phases such as iron oxides. Samples were prepared at a range of base pressures below 10 μTorr by pumping the chamber until a specific base pressure P was reached. The substrate was then heated, which raised the total pressure of the chamber to about 30 μTorr due to chamber outgassing. The chamber pressure was then pumped back down to P before deposition started. Therefore the pressure P during deposition consists of residual gas which includes oxygen and water vapor. Pre-deposition (5×10^3 laser pulses) was started with the shutter placed between the PLD target and the substrate, leading to an increase in the total chamber pressure by $\sim 2 \mu\text{Torr}$. After opening the shutter for film deposition (2×10^4 pulses), the chamber pressure gradually decreased and returned to near P at the end of the deposition. The substrate was cooled to room temperature at a rate of $-5^\circ\text{C min}^{-1}$ while pumping the chamber.

B. X-ray characterization

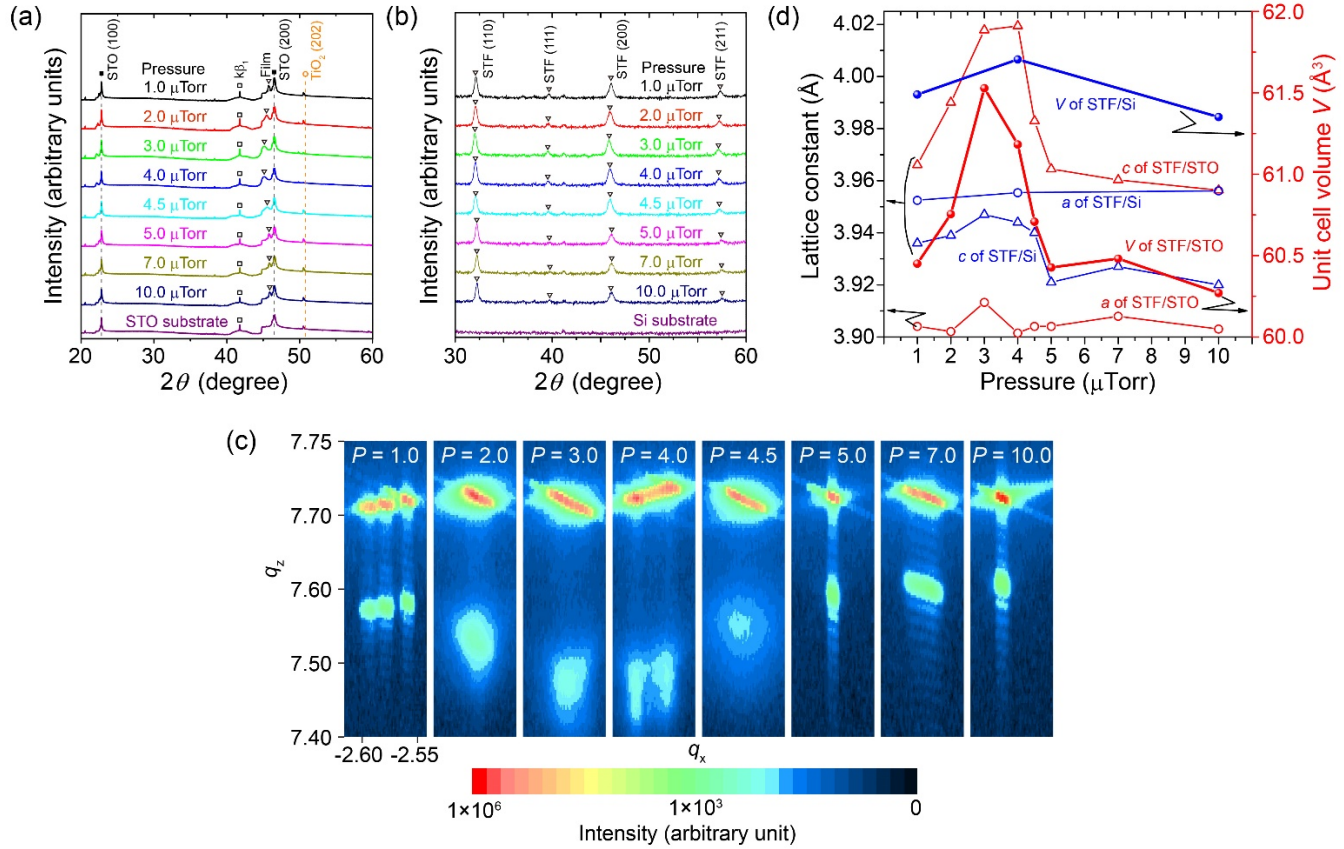
In-plane and out-of-plane lattice constants of single crystalline films on STO and polycrystalline films on Si were characterized by XRD (PANalytical, X'Pert) and two high-resolution XRD systems (HRXRD, Bruker-Axs D8 DISCOVER and Rigaku Smartlab). XRD patterns are shown in Figs. 1(a) and 1(b) for STF/STO and STF/Si, taken using a $\text{Cu-K}\alpha$ radiation source at a wavelength of 0.15418 nm. Figure 1(a) was measured by XRD (PANalytical, X'Pert), in which $\text{K}\beta_1$ peaks from the Cu source were observed. Figure 1(b) was measured by HRXRD (Rigaku Smartlab). The STF/Si samples were tilted by 1° to eliminate the strong substrate peak. The out-of-plane lattice parameters of STF on STO and on Si, $c_{\text{STF/STO}}$ and $c_{\text{STF/Si}}$, varied with the deposition pressure, and exhibited a maximum at $P = 3 - 4 \mu\text{Torr}$, with the variation stronger for the STF/STO. This behavior was also confirmed with the (002) peak obtained from XRD (PANalytical X'Pert). The TiO_2 (202) peak in Fig. 1(a) originated from the substrate.

Reciprocal space mapping (RSM) was used to measure the in-plane lattice parameter $a_{\text{STF/STO}}$ for the STF/STO. Grazing incidence diffraction (GID) was used to measure $a_{\text{STF/Si}}$ for the STF/Si samples grown at $P = 1, 4, \text{ and } 10 \mu\text{Torr}$ with the incident angle of the x-rays ω fixed at 0.4° . Figure 1(c) shows the RSM data for the STF/STO samples for the asymmetric (310) peak. The intense upper peak arises from diffraction from the STO substrate, and the bottom peak corresponds to the STF films. Multiple peaks are attributed to twinning of the substrates. The film and substrate peaks align in q_x indicating coherent cube-on-cube epitaxial growth of the STF films on the STO substrate, i.e. $a_{\text{STF/STO}} = a_{\text{STO}}$, whereas q_z gives the out-of-plane lattice parameter c , which differs for the film and substrate. The RSM data gave a standard deviation of $< 10^{-3} \text{ \AA}$ for $a_{\text{STF/STO}}$. The difference in values for c from different diffractometers, given by $(\text{HRXRD value} - \text{XRD value}) / \text{HRXRD value}$, was less than 0.1%, and the value of $c_{\text{STF/STO}}$ from RSM matched that measured by XRD. All the STF films on STO had out-of-plane lattice parameters greater than that of STO ($a_{\text{STO}} = 3.905 \text{ \AA}$) and were tetragonally distorted, with $(c/a)_{\text{STF/STO}} = 1.013$ to 1.030 indicating an in-plane compressive strain in the STF, similar to that found in prior work [16]. Figure 1(d) shows the variation of $a_{\text{STF/STO}}$, $c_{\text{STF/STO}}$, and unit cell volume $V_{\text{STF/STO}}$ with base pressure P .

For the samples of STF/Si, the in-plane and out-of-plane lattice parameters, $a_{\text{STF/Si}}$ and $c_{\text{STF/Si}}$, and the unit cell volume $V_{\text{STF/Si}}$ are shown in Fig. 1(d). The data gave a standard deviation of $\sim 6 \times 10^{-4} \text{ \AA}$ for a , and $2 \times 10^{-3} \text{ \AA}$ for c . The value of $a_{\text{STF/Si}}$ was $3.955 \pm 0.003 \text{ \AA}$ and showed little variation with P . Of the three STF/Si samples whose unit cell volume was measured, the one

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grown at $P = 4.0 \mu\text{Torr}$ showed the largest unit cell volume, the same trend as for films on the STO substrate. The value of $c_{\text{STF/Si}}$ was similar to or slightly smaller than $a_{\text{STF/Si}}$, i.e. $(c/a)_{\text{STF/Si}} = 0.990$ to 0.998 , depending on P . Thermal mismatch on cooling would lead to a tensile strain in the STF/Si film ($c/a < 1$), since Si has a lower thermal expansion coefficient than STF. This differs from the films on STO where lattice mismatch governs the strain state and produces an in-plane compressive strain in the STF, with $c/a > 1$.



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FIG. 1. Structural analysis of the STF films with XRD. (a) XRD patterns of STF/STO. The triangles show the film peaks. Black squares are peaks from bulk STO. A circle shows a TiO_2 peak present in the substrate scan. (b) XRD patterns of STF/Si. Positions of STF peaks are shown with triangles. There are no Si peaks in this angular range. (c) Reciprocal space mapping of single crystalline STF on STO substrate, plotted in q_z - q_x for the asymmetric (310) peak. (d) Lattice constants and unit cell volumes of STF films versus deposition pressure for both STF/STO and STF/Si.

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The larger unit cell volume of the films compared to that estimated for bulk STF without oxygen vacancies [$\text{SrTi}_{1.05}\text{Fe}_{0.35}\text{O}_3$, $V = \sim 60.13 \text{\AA}^3$ interpolated linearly from the unit cell volumes of STO ($a = 3.9051 \text{\AA}$, $V = \sim 59.55 \text{\AA}^3$) [48] and SrFeO_3 ($a = 3.9410 \text{\AA}$, $V = \sim 61.21 \text{\AA}^3$) [49] is a result of the greater oxygen vacancy content in the films compared to the bulk, which drives the Fe to lower valence states, expanding the lattice because of the larger ionic radii of the Fe. Other work on STO films [50] has showed changes in cation stoichiometry and hence lattice parameter at different laser focus conditions, but here we kept the deposition conditions nominally the same except for the base pressure, so we attribute changes in lattice volume to the oxygen vacancies and corresponding changes in Fe ionic radius. MacChesney *et al.* and Taguchi *et al.* showed that oxygen vacancies in $\text{SrFeO}_{3-\delta}$ and $\text{SrCoO}_{3-\delta}$ respectively increased the unit cell volume [51,52], and a sufficiently large oxygen deficiency ($\delta > 0.12$) promoted a cubic-to-tetragonal structural change in $\text{SrFeO}_{3-\delta}$ [42]. Perry *et al.* showed that the largest lattice parameter is obtained for STF annealed under the most reducing conditions, based on chemical expansion measurements [34]. Chakraverty *et al.* demonstrated that, for $\text{SrFeO}_{2.5}$ films on STO grown by PLD, the laser spot size, which affects the growth process, kinetics and stoichiometry, controlled the lattice parameter [53].

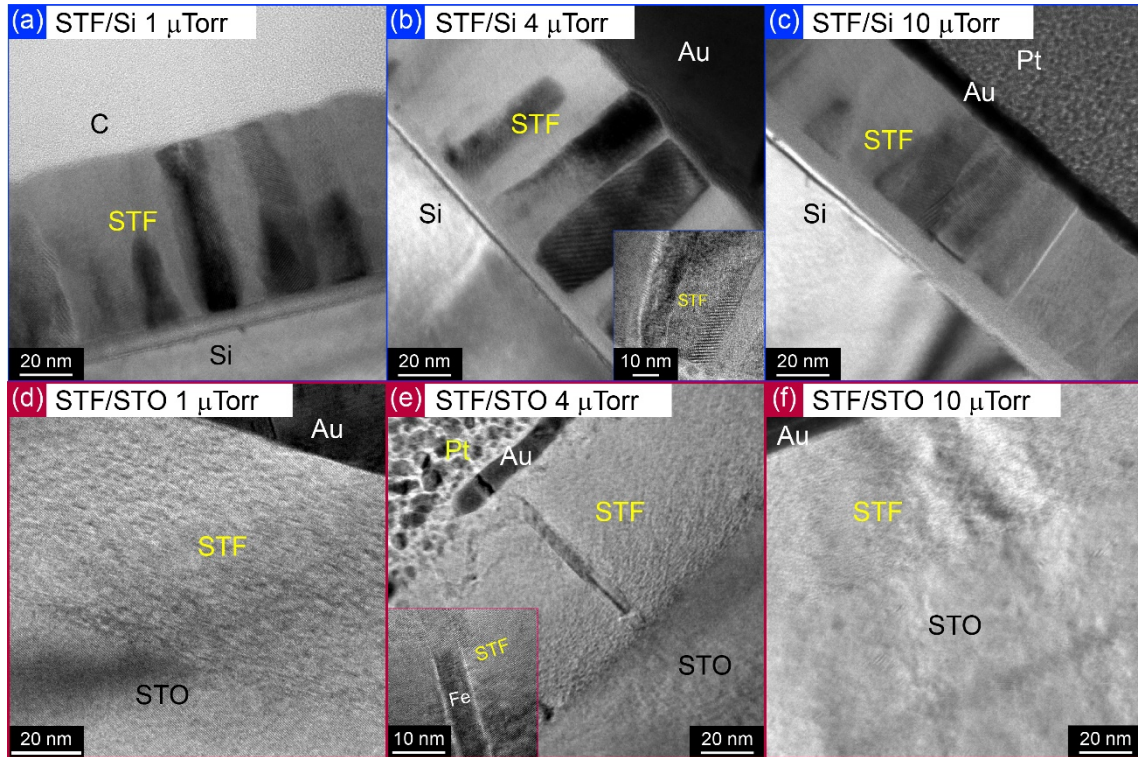
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C. Film morphology.

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Cross-sectional TEM images of STF/Si and STF/STO grown at $P = 1, 4$ and $10 \mu\text{Torr}$ are given in Fig. 2. All three STF/Si films had a polycrystalline columnar microstructure, and energy-dispersive x-ray spectroscopy (EDX) mapping of the $4 \mu\text{Torr}$ sample, Fig. 3, indicates a spatial variation in the Fe content, with higher Fe content corresponding to a few of the columnar features. In

132 agreement with the Mössbauer spectroscopy (described below), there was no clear evidence from high resolution TEM that these
 133 columns were metallic Fe, and we presume they represent STF with a higher Fe content than neighboring grains. A similar inho-
 134 mogeneity was found at $P = 1 \mu\text{Torr}$, but at $10 \mu\text{Torr}$ the Fe was uniformly distributed. The compound $\text{SrTi}_{1-x}\text{Fe}_x\text{O}_{3-\delta}$ is stable
 135 throughout the composition range [13,14], therefore we assume that the inhomogeneity is different in origin from that seen in spin-
 136 odal decomposition such as that of Cr-rich (Zn, Cr)Te [54], In-rich (Ga, In)N [55], or (Mn, Ga)As [56] systems. In comparison,
 137 the STF grown on STO was single-crystal but showed contrast that indicated small scale structural inhomogeneity, possibly repre-
 138 senting layered vacancy ordering as seen in brownmillerite-structured $\text{SrFeO}_{2.5}$ [57] and in $(\text{La,Sr})\text{CoO}_3$ [58,59]. At $P = 4 \mu\text{Torr}$, a
 139 few straight, vertical nanopillars were observed perpendicular to the substrate within the perovskite matrix. Lattice imaging re-
 140 vealed that the pillars were metallic α -Fe. The pillars were sparsely distributed, with spacings of $\sim 200 \text{ nm}$ in the TEM image of a
 141 lamella $\sim 20\text{--}50 \text{ nm}$ thick. This suggests a density of $100\text{--}250$ pillars per μm^2 .
 142 The pillar width was $3\text{--}5 \text{ nm}$, giving an estimate of the volume fraction of metallic Fe of $0.1\text{--}0.4\%$. This volume fraction is small,
 143 but it could contribute a significant amount of the net magnetization because metallic Fe has a high saturation magnetization of
 144 1700 emu cm^{-3} . However, the majority of the Fe remains in the perovskite, e.g. the formation of even $0.5 \text{ vol.}\%$ metallic Fe would
 145 deplete Fe from $\sim 8\%$ of the STF volume. Films grown on STO at $P = 1 \mu\text{Torr}$ and $10 \mu\text{Torr}$ had no pillars, and the Fe was uniform-
 146 ly distributed.



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 148 FIG. 2. Transmission electron microscopy of STF samples. Cross-sectional TEM images of STF/Si deposited at $P =$ (a) $1 \mu\text{Torr}$, (b)
 149 $4 \mu\text{Torr}$, and (c) $10 \mu\text{Torr}$. Cross-sectional TEM images of STF/STO deposited at $P =$ (d) $1 \mu\text{Torr}$, (e) $4 \mu\text{Torr}$, showing a Fe rod,
 150 and (f) $10 \mu\text{Torr}$. Specimens were covered with conductive materials, either Au or C.

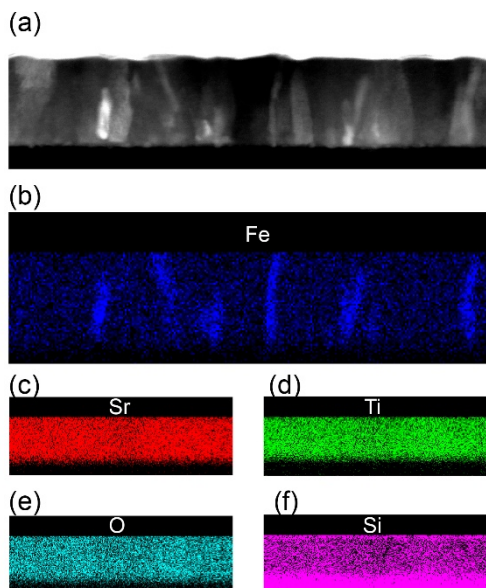


FIG. 3. Composition analysis of STF/Si. (a) STEM images and STEM-EDX element mappings of STF deposited on Si at $P = 4 \mu\text{Torr}$. STEM-EDX Element map of (b) Fe, (c) Sr, (d) Ti, (e) O, (f) Si. A Sr peak overlaps the Si peak leading to a false signal for the region of the film in (f).

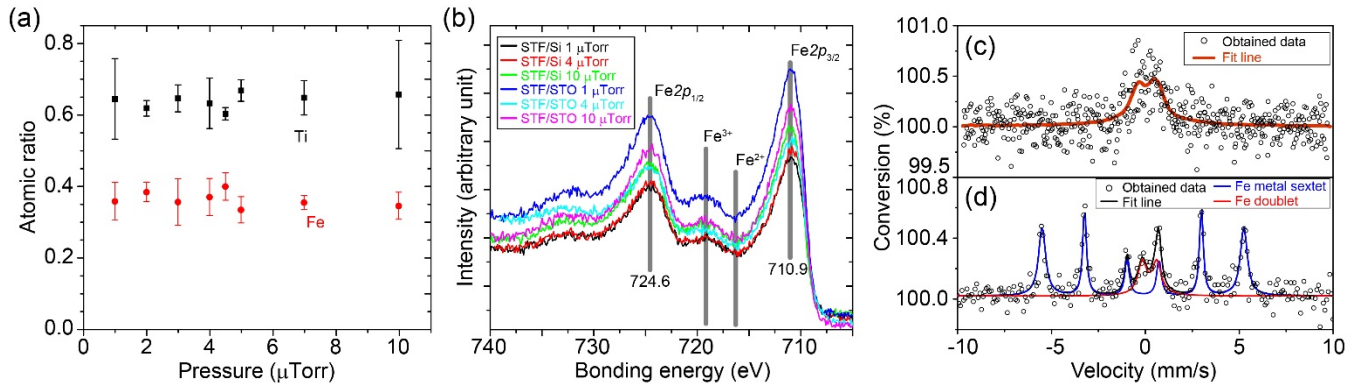
D. Fe valence state.

Measurement of the atomic ratio of Ti and Fe is shown in Fig. 4(a) from energy-dispersive x-ray spectroscopy (EDS, FEI Philips XL 30), confirming that there was no systematic change in the ratio of Fe:Ti ($= 0.35:0.65$) with P .

The Fe valence state was characterized by conversion electron Mössbauer spectrometry (CEMS) and by x-ray photoelectron spectroscopy (XPS). CEMS showed a difference between two films grown at $P = 2 \mu\text{Torr}$ on different substrates, as shown in Figs. 4(c), and 4(d). For the STF/Si, a weak paramagnetic signal of Fe^{3+} was detected ($\sim 0.7\%$ max emission). The signal may be fitted to a singlet (Gaussian) or a doublet (2 pseudo-Voigts) as shown in Fig. 4(c), yielding an isomer shift relative to $\alpha\text{-Fe}$ of $0.25 \pm 0.04 \text{ mm s}^{-1}$ and a quadrupole splitting of $0.89 \pm 0.08 \text{ mm s}^{-1}$. This signal may arise from Fe^{3+} associated with oxygen vacancies [60]. No other signals were resolved.

The STF/STO showed 0.5–0.6 % emission after optimization. Unlike the sample on Si, the STF/STO showed a metallic iron magnetic phase, identified not just because of the presence of a sextet but also because of the isomer shift of $0.00 \pm 0.02 \text{ mm s}^{-1}$, equal to that of $\alpha\text{-Fe}$ (Fig. 4(d)). The peak-intensity ratio of the sextet state indicates that the iron is not uniformly magnetized perpendicular to the substrate [61–63]. There was also a paramagnetic ferric doublet with an isomer shift of $0.35 \pm 0.04 \text{ mm s}^{-1}$ that accounted for 23% of the peak area. A measurement using Auger electrons sensitive to the top 20–30 nm of the film showed a lower peak area fraction (15%) for the paramagnetic iron suggesting a depth dependence of the iron valence state. These results indicate that metallic Fe was present in the STF/STO but not in the STF/Si grown at $P = 2 \mu\text{Torr}$.

Figure 4(b) shows XPS results in which the Fe peaks were similar over the range of deposition pressures and the two substrate types. The peak positions were calibrated so that the Cu peak was present at 284.8 eV. There were no significant differences in the Sr, Ti, and O XPS peaks. The satellite peaks around the Fe $2p_{3/2}$ and $2p_{1/2}$ doublet indicate the presence of Fe^{3+} but not Fe^{2+} , similar to epitaxial BiFeO_3 [64] and iron oxides [65]. The lack of a metallic Fe peak in the $4 \mu\text{Torr}$ sample on STO differs from the TEM results and from the Mössbauer analysis of the $P = 2 \mu\text{Torr}$ sample. Since XPS is surface-sensitive, we assume that the top parts of the Fe nanorods at the surface would be subject to oxidation, or their very small area coverage may have precluded the observation of a metallic Fe peak.

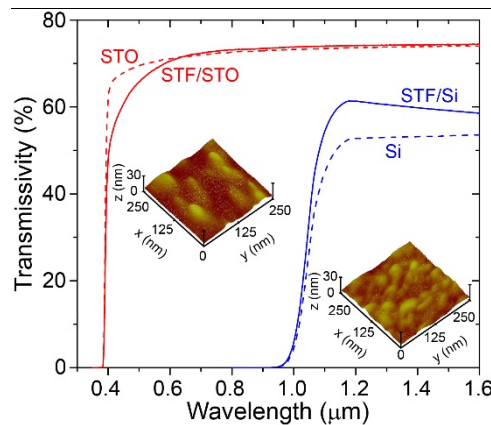


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FIG. 4. Composition analysis of the STF films. (a) Atomic ratio of Fe to Ti in STF/STO measured by EDS. Error bars show the standard deviation. (b) XPS peaks from Fe $2p$ in STF films on STO and Si substrates. Mössbauer spectroscopy of (c) STF/Si, and (d) STF/STO, both deposited at $P = 2 \mu\text{Torr}$, measured over the depth of the films. The STF film on the Si substrate does not show the metal sextet phase, but instead, a weak paramagnetic signal.

186 187 E. Optical and magnetic characterization

188 Transmissivity of the films on the two substrates from visible to near-IR wavelengths is shown in Fig. 5. For energies below the
189 bandgap, the transmissivity of STF/Si was higher than that of bare silicon because of the anti-reflection effect that arises from in-
190 troducing a lower refractive index film on a higher refractive index substrate. The transmissivity of STF/STO and bare STO were
191 similar except for energies just below the bandgap where the STF/STO became absorbent.

192 Atomic force microscope (AFM) images of the STF/Si and STF/STO grown at $P = 4 \mu\text{Torr}$ are shown as insets in Fig. 5. The films
193 had a root-mean-square roughness of 1.8 and 2.2 nm, respectively, leading to reflective film surfaces. The STF/Si grown at $P = 1, 4,$
194 and $10 \mu\text{Torr}$ had similar surface topography, with in-plane feature sizes of 20–40 nm. In contrast, the STF/STO grown at $P = 1$
195 μTorr and $10 \mu\text{Torr}$ was much smoother than the film grown at $4 \mu\text{Torr}$.



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FIG. 5. Optical properties of STF films. Transmission spectra of STF/Si, STF/STO, and their substrates; the insets show the AFM images of the surface topography.

200 Figure 6 shows the room temperature magnetic hysteresis loops from vibrating sample magnetometry (VSM) for films on both sub-
201 strates as a function of P . Linear substrate signals were subtracted. Uncoated STO substrates subjected to thermal cycling in vacu-
202 um in the PLD chamber similar to the thermal cycling during film growth showed a diamagnetic response with little change on
203 annealing. For both substrates, the films grown at $P = 4.0 \mu\text{Torr}$ showed the largest saturation magnetization, while films grown at
204 or above $P = 5 \mu\text{Torr}$ did not exhibit a hysteresis loop. The magnetic easy axis was along the out-of-plane direction, with switching
205 fields of 3–4 kOe and a high remanence. The hysteresis loop shape, switching field, and the anisotropy field are generally consistent
206 with those seen in previous studies of STF/STO [16,27,28]. The STF/STO grown at $P = 4 \mu\text{Torr}$ had $M_s = 17 \text{ emu cm}^{-3}$, whereas—
207 remarkably—the polycrystalline STF/Si had $M_s = 28 \text{ emu cm}^{-3}$, which is higher by a factor of nearly two and corresponds to 0.48
208 μ_B/Fe . In the STF/STO, the metallic Fe would contribute $\sim 2\text{--}6 \text{ emu cm}^{-3}$ based on the estimated volume fraction.

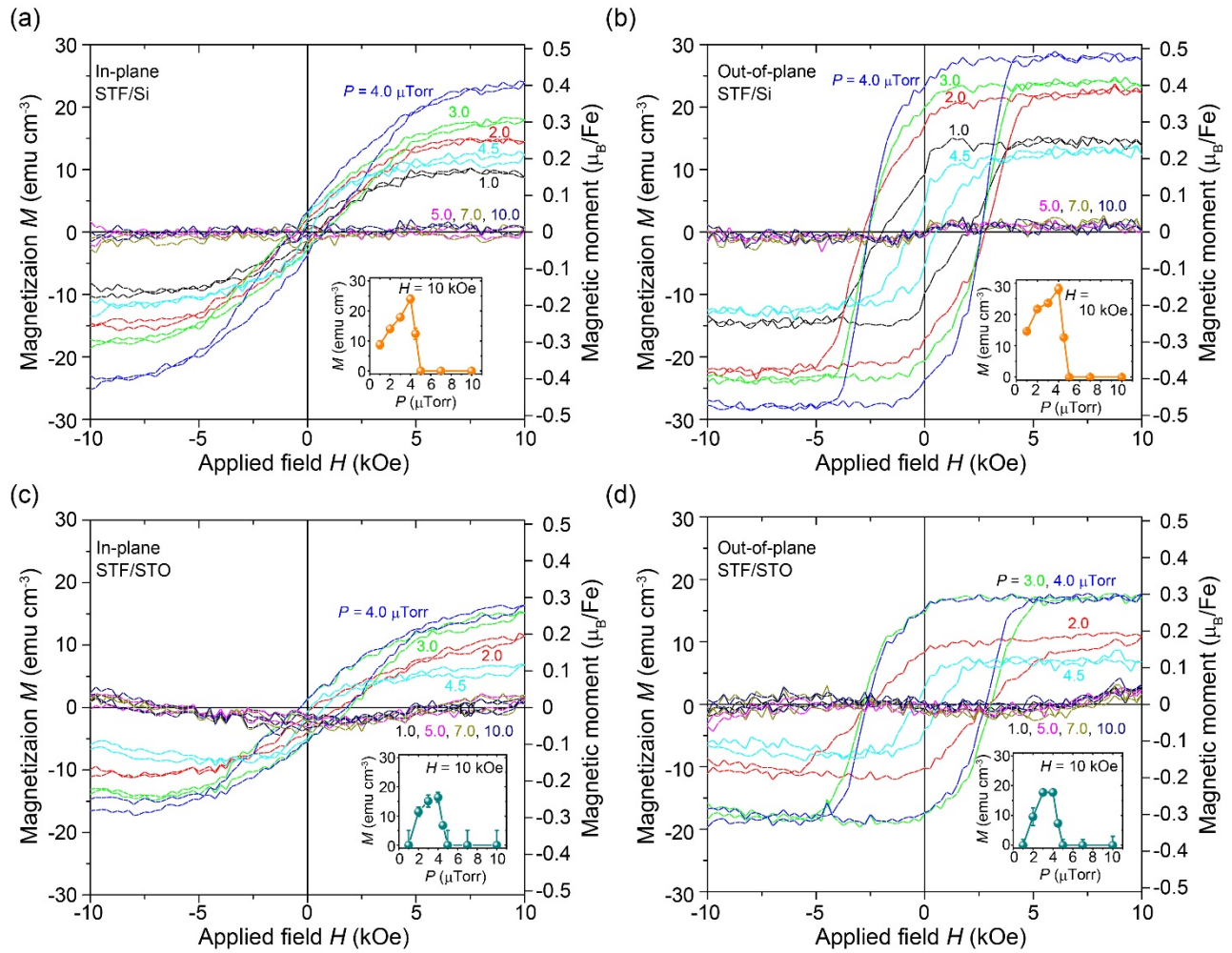


FIG. 6. Magnetic properties of STF films measured by VSM. (a),(b) Magnetic properties of STF/Si specimens (c),(d) Magnetic properties of STF/STO specimens, (a),(c) in-plane and (b),(d) out-of-plane. Insets show the dependence of the magnetization on pressure at $H = 10$ kOe.

The magneto-optical response of STF (FR loop versus applied magnetic field) was measured at a wavelength of 1550 nm by the Faraday cell modulation method [65] and is shown in Fig. 7. The field and light were perpendicular to the film in the Faraday measurement, and the Faraday loop showed a comparable shape and coercivity (~ 3 kOe) to the out-of-plane magnetic hysteresis loops shown in Fig. 6. Low-spin ($S = 1$, $2 \mu_B$ per ion) Fe^{4+} can provide splitting of the two circular modes of a linearly polarized optical wave required for FR [29]. The saturation FR angle of STF/Si was approximately two times larger than that of STF/STO, reaching $-1900 \text{ }^\circ\text{cm}^{-1}$, i.e. the FR scaled with the saturation magnetization. This FR is $\sim 60\%$ of that reported for single crystalline cerium-substituted yttrium iron garnet (CeYIG , $\text{Ce}_1\text{Y}_2\text{Fe}_5\text{O}_{12}$) [66,67] at 1550 nm. CeYIG is a candidate material for magneto-optical devices in the near-IR. (CeYIG films [4,5,68-70] differ from STF in having an in-plane easy axis.)

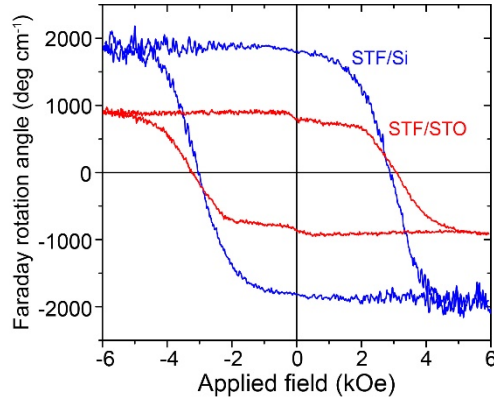


FIG. 7. Magneto-optical properties of STF films. FR loops of STF/Si and STF/STO samples at a wavelength of 1550 nm.

F. Discussion

These results illustrate a sensitivity of the STF structure and the optical and magnetic properties to both the pressure during deposition and the substrate type. Both STO and SrFeO₃ structures can accommodate significant amounts of oxygen deficiency, maintaining a perovskite-like structure with oxygen vacancies that may be disordered or that can be arranged in layers, e.g. brownmillerite SrFeO_{2.5} when $\delta=0.5$. The unit cell volume increases with δ and there are dramatic changes in conductivity and other properties with δ [11,15,20,22-24,72]. Vacancies can even be introduced into an STO substrate at low pressure and high temperature [73], which affects the surface of the substrate prior to film growth.

The oxygen content of the films and therefore δ is difficult to quantify because the sample volume is too small for thermogravimetric analysis, although other methods such as photoluminescence, direct imaging, or measurements of cation valence may be applicable [74,75]. However, Rothschild *et al.* [14] showed that Fe³⁺ was the dominant valence state in STF over a range of pressures and temperatures including those corresponding to the growth conditions, i.e. the composition can be written SrTi_{1-x}Fe_xO_{3-(x/2)- γ} with γ representing the deviation from a state containing all Fe³⁺. The presence of Fe²⁺ became significant at extremely low oxygen pressures, e.g., below 10⁻⁹ Torr at 600°C, whereas Fe⁴⁺ was present at higher pressures, e.g., above 10 mTorr. Rodriguez *et al.* showed that a mixture of Fe³⁺ and Fe⁴⁺ was present in STF after synthesis at 1300°C in oxygen [76], and Ferreira suggested that some Fe⁴⁺ was present at room temperature [20]. It is not clear how well the PLD growth conditions correspond to these equilibrium conditions, but we expect that the oxygen content will be kinetically trapped after cooling the samples from the growth temperature, implying that the oxygen content and the average Fe valence state in the films will be lower for films grown at a lower base pressure.

The formation of sparsely distributed metallic Fe nanorods was inferred in the $P = 2 \mu\text{Torr}$ and $4 \mu\text{Torr}$ STF/STO samples. This was not seen in our previous work on STF [16], but there have been several other observations of metallic transition metal nanorods forming in an oxide matrix, notably Fe in a (non-perovskite) LaSrFeO₄ matrix formed from the deposition of LaSr_{0.5}Fe_{0.5}O₃, and Co, Ni or Fe in ceria or STO by codeposition of the matrix phase with a transition metal oxide [77-79]. In the $P = 4 \mu\text{Torr}$ STF/STO, it is possible that the low base pressure combined with the large tetragonal distortion due to epitaxy promotes the precipitation of a fraction of the Fe as a strain relief mechanism that was not seen in the non-epitaxial films on Si. The precipitation of the small volume fraction of metallic Fe would lead to an excess of Sr in the perovskite matrix that could be accommodated through additional SrO layers as in Ruddlesden-Popper phases without disrupting the overall perovskite structure. In contrast, in the films on Si it appears that all the Fe was present within the perovskite lattice. The Fe distribution did, however, become less homogeneous at low base pressure. It is not clear why the STF unit cell volumes decreased for $P < 4 \mu\text{Torr}$. This may indicate a different strain relaxation mechanism becoming important, or a structural change due to the ordering of vacancies or the formation of Ti³⁺.

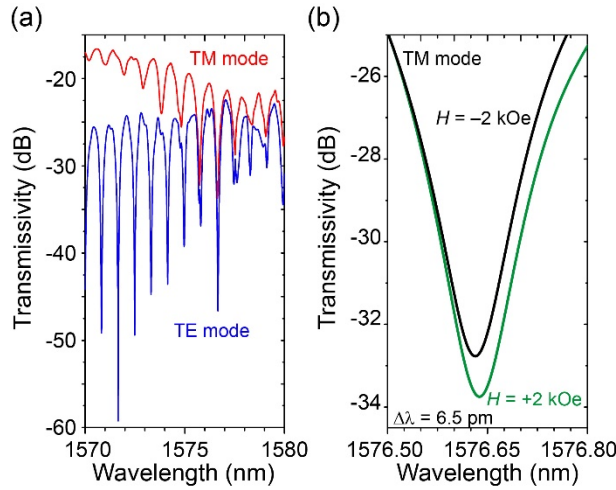
In previous work, we have suggested that oxygen-deficient STF exhibits mixed valence Fe ions, leading to both ferromagnetic and antiferromagnetic interactions between nearest-neighbors. A range of other Fe-based perovskites including Sr₂FeMoO₆ and Ba₂FeReO₆ also display room temperature magnetism that originates on the Fe spins [80-82]. Moreover, the magnetic moment of Fe ions is dramatically affected by adjacent oxygen vacancies that break the symmetry of the oxygen coordination octahedron, as predicted theoretically in STCo [83]. Film strain leads to magnetoelastic anisotropy, which can orient the overall direction of magnetization in the film, accounting for the out-of-plane easy axis for STF/STO [16]. The resulting net magnetic moment of the STF and the hysteresis behavior is therefore highly dependent on the concentration and arrangement of the oxygen and Fe and the strain state, as well as the presence of Fe nanorods, and is expected to vary with all the film deposition conditions including P . In STCo, changes in P were also found to affect the magnetic moment [22].

The most striking finding in the present work is the higher magnetization and FR in films made on Si compared to those on STO. The films differ in their microstructure and strain state, but may also have subtle differences in oxygen content, vacancy clustering, or Fe distribution despite being deposited simultaneously; this could result from different surface kinetics or surface chemistry dur-

269 ing film nucleation, or differing substrate temperatures due to the differences in emissivity and thermal conductivity between the Si
 270 and STO substrates. The magnetic effects in STF/Si appear not to originate from metallic Fe, and are therefore intrinsic to the sub-
 271 stituted perovskite. Metallic behavior has been calculated for STO surfaces [84], suggesting that the grain boundaries in the STF
 272 may play a role in its electronic properties. Unlike the STF/STO, which has a significant tetragonal distortion ($c/a > 1$) leading to
 273 magnetoelastic anisotropy [27,85], the polycrystalline STF/Si has little strain, suggesting that the origin of its magnetism is micro-
 274 structural (influenced by grain boundaries, oxygen content, vacancy clustering, or the inhomogeneous Fe distribution observed in
 275 Figs. 2(a-c) and 3(b)) rather than magnetoelastic.

276
 277 **III. INTEGRATED MAGNETOOPTICAL ISOLATOR**

278 The polycrystalline STF/Si is suitable for magneto-optical devices because it is expected to grow on a variety of substrates and it has
 279 a large remanent Faraday rotation angle. As an illustration of the integration of polycrystalline STF into a magneto-optical device, a
 280 ring resonator was prepared from a silicon-on-insulator wafer consisting of a racetrack placed adjacent to a straight waveguide,
 281 similar to the devices shown in Refs. [4,5] When light passing through the waveguide is resonant with the racetrack (i.e., when the
 282 racetrack circumference is an integral number of wavelengths), the light couples into the racetrack, and there is a drop in transmit-
 283 tance through the waveguide, as shown in Fig. 8. If the racetrack is clad on top with a magneto-optical material magnetized perpen-
 284 dicular to the waveguide, the transverse magnetic (TM) mode, but not the transverse electric (TE) mode, experiences a nonreciprocal
 285 phase shift (NRPS). This leads to a different resonant wavelength for clockwise and counterclockwise propagating TM light,
 286 which forms the basis of an isolator.



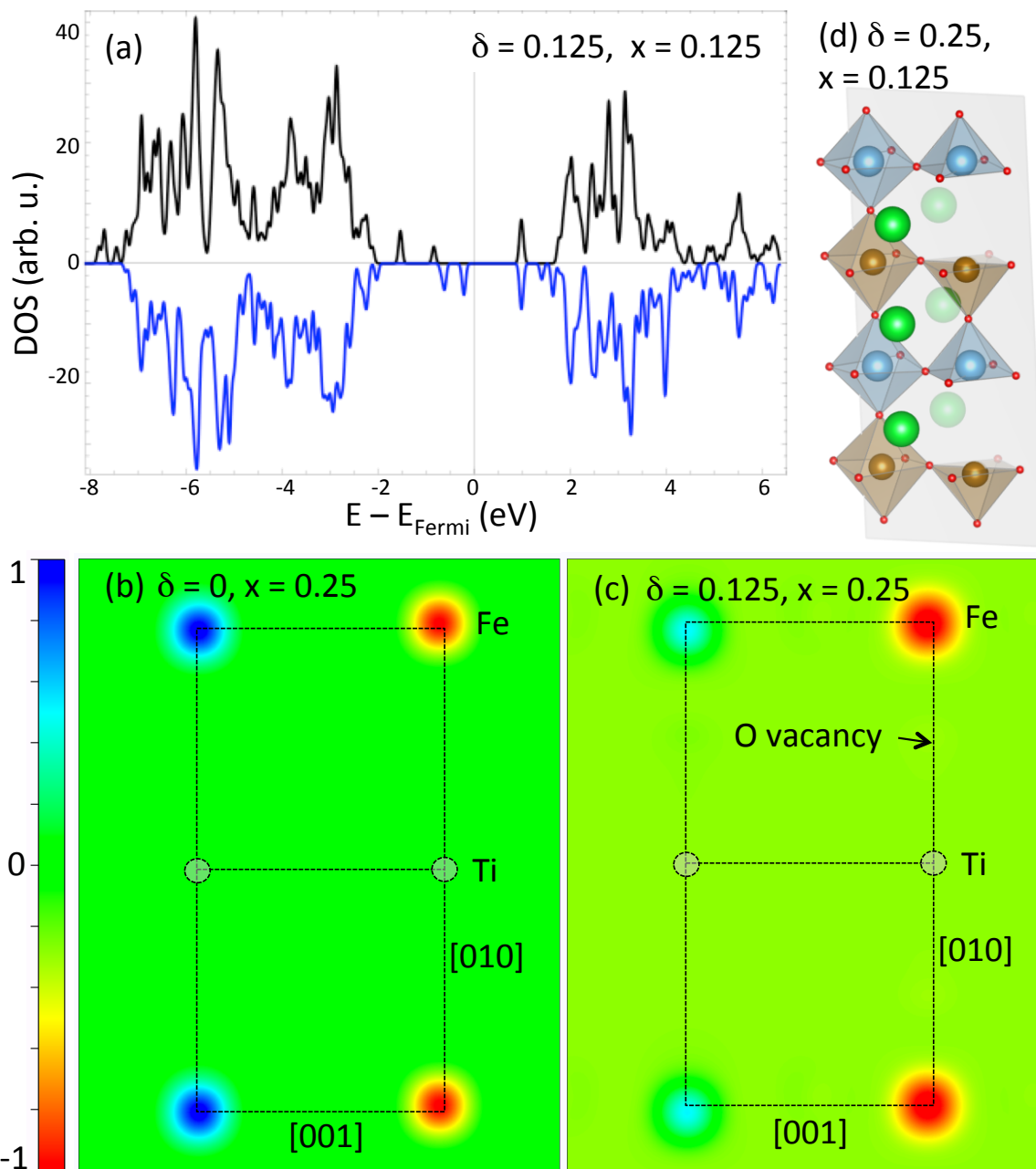
287
 288 FIG. 8. Integration of STF on a waveguide device. (a) Resonant peaks for TE and TM modes at wavelengths between 1570 nm and
 289 1580 nm. (b) Example of a peak shift for the TM mode that showed a NRPS of 6.5 nm when the field H direction was reversed.

290
 291 The waveguides had a thickness of 250 nm and a width of 450 nm. The racetrack was 290 μm long and 90 μm wide. A 200- μm -
 292 long, 20- μm -wide window was opened in the silica cladding of one of the sides of the racetrack and STF (at $P = 4$ μTorr) was de-
 293 posited over the sample, so that the STF contacted the waveguide directly within the window. The transmittance of the wave-
 294 guide/resonator was measured at a wavelength of around 1550 nm for a magnetic field of ± 2 kOe applied in-plane, perpendicular to
 295 the side of the racetrack. The resonant wavelength of both the TM and TE modes varied between successive measurements by up to
 296 10 pm because of thermal drift or vibration, but the TM mode showed an NRPS of ~ 4 pm compared to the TE mode when the sign
 297 of the applied field was changed.

298
 299 Similar devices made with CeYIG cladding [5] ($\text{FR} \sim 1300$ $^\circ\text{cm}^{-1}$) with in-plane magnetization exhibited a NRPS of ~ 20 pm. The
 300 lower NRPS in the STF devices is a result of incomplete in-plane saturation, which requires a field > 5 kOe. Based on the hysteresis
 301 loops, a 2 kOe in-plane field would lead to an in-plane magnetization of approximately 1/3 of the saturation magnetization. The FR
 302 scales with the magnetization, so we expect the STF to produce an NRPS of 1/3 of what would be produced at in-plane saturation.
 303 The NRPS of the STF devices is in reasonable agreement with the expected NRPS, considering the geometry of the resonator and
 304 the magnitude of the FR. The absorption of the STF at a wavelength of $\lambda = 1550$ nm was 31 ± 2 dB cm^{-1} , derived as shown in [69].
 305 Hence, the figure of merit defined as the ratio of saturation FR/absorption was 58 $^\circ\text{dB}^{-1}$, which is good compared with other thin
 306 film magneto-optical materials [17,33].

307
 308 **IV. ELECTRONIC STRUCTURE CALCULATIONS**

309 We now present a brief discussion of the theoretical predictions for the electronic structure and the change of the lattice parameters
 310 as a function of the chemical pressure created by oxygen vacancies of STF based on hybrid density functional theory (DFT) [83], as
 311 described in the methods section. All possible vacancy and Fe configurations for STF with $x = 0.125$ or 0.25 were evaluated.
 312
 313 From Fig. 9(a), we find that STF with $\delta = 0.125$ and $x = 0.125$ (one Fe atom and one vacancy in the $2 \times 2 \times 2$ perovskite supercell) is
 314 a semiconductor with a band gap of ~ 1.1 eV. The e_g orbitals are partially occupied, which gives rise to the ferrimagnetism. From
 315 molecular orbital theory, we find that the high-low spin-gap energy is ~ 70 meV, which is actually larger than the ~ 40 meV required
 316 to take a spin to the e_g from the t_{2g} level [30]. A detailed analysis of the spin states in this system will be discussed in a subsequent
 317 publication. We confirmed the oxidation states were Fe^{2+} and Ti^{4+} rather than both ions being $3+$, and the Ti^{4+} magnetic moment is
 318 negligible.
 319



320
 321
 322 FIG. 9. DFT calculations. (a) Total density of states for $\text{SrTi}_{0.875}\text{Fe}_{0.125}\text{O}_{2.875}$ (high spin Fe) obtained with HSE06. The supercell
 323 contains one Fe ion and one neighboring vacancy. (b) Spin density (HSE) projected onto the (100) plane for $\text{SrTi}_{0.75}\text{Fe}_{0.25}\text{O}_3$ in which
 324 the two nearest-neighbor Fe ions are aligned in the $[001]$ direction, showing clearly their antiferromagnetic ordering. (c) Spin densi-

325 ty (HSE) projected onto the (100) plane for $\text{SrTi}_{0.75}\text{Fe}_{0.25}\text{O}_{2.875}$ with an oxygen vacancy adjacent to one of the two Fe ions per unit
326 cell. In both cases (b) and (c), the second-nearest Fe neighbors are also depicted and the color scale indicates the spin density nor-
327 malized to the largest magnetic moment. The ferrimagnetic order in the O-deficient system is clear in (c). (d) Image showing the
328 model in (c) in which the atomic positions are visible. The plane shown in (c) bisects the model passing through the Fe and Ti sites.
329 Blue: Fe; brown: Ti; green: Sr; red: O.

330

331 When $x = 0.25$, the two Fe ions can be arranged along [001], [110], or [111]. In each case, the Fe-Fe distances are $\sim 0.9x$ the Ti-Ti
332 distance in STO, and the final unit cell is distorted from cubic symmetry. In the $\delta = 0$ case the Fe ions have an average moment of
333 $3.7 \mu_B$, with an antiferromagnetic (AF) ground state in the Fe-[001] arrangement. For the [110] and [111] arrangements where the
334 Fe ions are further separated, the lowest energy ferromagnetic (FM) and antiferromagnetic (AF) states are almost degenerate within
335 a small energy range < 40 meV. The preponderance of [110] and [111] configurations in a crystal with random Fe site distribution
336 suggests an overall low moment due to dominant AF interactions.

337

338 An oxygen vacancy ($\delta = 0.125$) leads to a significant increase in the volume of the unit cell compared to $\delta = 0$, in agreement with
339 experiment. The volume increase is not due to the Fe-Fe interaction but to the chemical pressure created by the vacancy. When
340 calculating the ground state for $\delta = 0.125$, the spin and valence of the two Fe ions were initialized in all possible combinations (i.e.
341 both Fe^{3+} , one Fe^{4+} and one Fe^{2+} , high and low spin, and FM and AF) and the lowest energy state after relaxation was defined as the
342 ground state. The low spin states tended to shift to high spin with ~ 4.1 – $4.2 \mu_B$, with the two Fe spins coupled AF in most but not all
343 cases. However, even the AF-initialized cells had a net moment, i.e., they were ferrimagnetic, because the spin at each Fe location
344 was not identical owing to their different locations with respect to the oxygen vacancy.

345

346 In the Fe-[001] case, the lowest energy configuration is one where the vacancy is between the two Fe ions, which eliminates the
347 superexchange between the Fe ions that coordinate the vacancy. The magnetic moment was $\sim 0.2 \mu_B/\text{Fe}$. In the Fe-[110] case, the
348 two possible vacancy positions lead to similar energies, and the magnetization in the ground state is 0.3 – $0.4 \mu_B/\text{Fe}$. In the more
349 symmetric case of Fe-[111], the FM and AF configurations are almost degenerate (i.e., < 0.1 meV) because of the large separation
350 between the Fe atoms. The final magnetic moment of the AF-initialized arrangement is once again 0.1 – $0.2 \mu_B/\text{Fe}$.

351

352 To better understand the effects of the vacancies on the magnetic behavior, we calculate the HSE spin density for a system with $x =$
353 0.25 and $\delta = 0$ or $\delta = 0.125$. Figure 9(b) shows the spin density projected onto the (100) plane for $\text{SrTi}_{0.75}\text{Fe}_{0.25}\text{O}_3$ in which the two
354 Fe ions are aligned in the [001] direction. The AF ordering of the two Fe ions is seen from the opposite sign but equal value of the
355 spin density. In Fig. 9(c), a vacancy is introduced, i.e. the composition is $\text{SrTi}_{0.75}\text{Fe}_{0.25}\text{O}_{2.875}$ with the vacancy placed adjacent to one
356 Fe ion but not between the two Fe ions. The magnetic moment of the Fe next to the vacancy is enhanced, as evident by the slightly
357 larger radius of the red spin-density projections, while the other Fe which is completely O-coordinated has a smaller magnetic mo-
358 ment (blue) coupled antiferromagnetically to the larger moment of the first Fe. While the two Fe magnetic moments per unit cell in
359 the first case are equal in magnitude, in the O-coordinated Fe case there is a difference of 0.1 – $0.3 \mu_B/\text{Fe}$ between the moments
360 (i.e. the system is ferrimagnetic), in accordance with our previous discussion. These results have been qualitatively con-
361 firmed using LMTO (linear muffin-tin orbital). In the case of Fig. 9(c) the magnetic moment of the incompletely coordinated
362 Fe was higher, and this is the case for most of the possible combinations of Fe valence and spin state. However, a few con-
363 figurations with a slightly higher energy showed an increase of the moment of both Fe ions or even an increase just of the
364 magnetic moment of the completely coordinated Fe ion.

365

366 The STF film is expected to comprise randomly distributed Fe ions and vacancies, and we would therefore expect a variety
367 of nearest neighbor configurations and resulting interactions to be present, including those addressed in the modeling. The
368 crystal would then exhibit a relatively low net magnetic moment, dominated by AF coupling, analogous to a ferrimagnet but
369 without long range order. The presence of vacancies is predicted to increase the unit cell volume, raise the magnetic moment at the
370 Fe sites and to lead to a net moment even when AF interactions are dominant. These predictions are broadly in line with the exper-
371 imental results.

372

373

V. CONCLUSION

374

375 In conclusion, STF ($\text{SrTi}_{0.65}\text{Fe}_{0.35}\text{O}_{3-\delta}$) films grown on Si or STO substrates by PLD showed a strong dependence of microstructure
376 and magnetic properties on the base pressure during deposition. At an optimum base pressure for deposition ($P = 4 \mu\text{Torr}$) the films
377 showed room temperature magnetism of up to $0.53 \mu_B/\text{Fe}$ with out-of-plane magnetic anisotropy, and a coercivity of 3 kOe as well
378 as a FR of $-1900 \text{ }^\circ\text{cm}^{-1}$ at a wavelength of 1550 nm. STF grown on STO at the optimum base pressure of $P = 4 \mu\text{Torr}$ showed a
379 low ($< 0.5\%$) volume fraction of metallic Fe nanorods not present at other pressures that contribute to the magnetic signal, but the
380 polycrystalline STF films grown on Si showed 65% greater magnetization and FR compared to the epitaxial films on STO. There
381 was no evidence of metallic Fe in the STF/Si, indicating that the magnetic and magneto-optical properties are intrinsic to the substi-
tuted perovskite. Polycrystalline STF was grown onto a silicon ring resonator, and its FR produced a non-reciprocal phase shift.

382 First-principles calculations showed that oxygen vacancies increase both the unit cell volume and the magnetic moment of the Fe
383 ions. The dominant interactions are antiferromagnetic, leading to a material with a net magnetization below about $0.5 \mu_B/\text{Fe}$, which
384 is reasonable compared with the experimental data. These results illustrate the important role of oxygen vacancies in determining
385 the magnetic properties and structure of a Fe-substituted perovskite, and the integration of the perovskite in magneto-optical devices.
386

387 388 APPENDIX A: TARGET PREPARATION

389 SrCO_3 (99.99%), TiO_2 (99.99%) and Fe_2O_3 (hematite, 99.945%) powders were stoichiometrically mixed, ball milled for 24 hours,
390 and calcined at 1200°C for 5 hours, showing a single perovskite phase. The powder was pressed into a 1-inch-diameter pellet and
391 sintered at 1300°C for 5 hours.

392 393 APPENDIX B: SAMPLE PREPARATION FOR TEM

394 The samples were prepared using a focused ion beam (FEI-600), and then imaged on a JEOL 2010F field emission TEM at 200 kV
395 acceleration voltage. The element distribution in the sample was mapped by STEM EDX.

396 397 APPENDIX C: X-RAY DIFFRACTION

398 For STF/STO, the PANalytical X'pert was used. The wavelength was $\text{Cu-K}\alpha$ ($\lambda = 1.540598 \text{ \AA}$), the source current was 40 mA, the
399 voltage was 45 kV, and the scan step in 2θ was 0.017° . There was no offset of ω . For STF/STO reciprocal space maps, the Bruker-
400 Axs D8 DISCOVER was used with $\text{Cu-K}\alpha$ radiation. The x-ray beam was monochromated with the $\text{Ge}(220)\times 4$ and the Gobel mirror
401 slit was 0.8 mm. The first and second monochromator slits were 0.2 mm and 1 mm. For STF/Si, the Rigaku Smartlab was used
402 because of its capability for in-plane GID. The wavelength was $\text{Cu-K}\alpha$ with a tube current of 200 mA and a voltage of 45 kV. The
403 step of the 2θ goniometer was 0.024° , and the incident angle of the x-rays ω was fixed at 0.4° .

404 405 APPENDIX D: MÖSSBAUER SPECTROSCOPY

406 ^{57}Fe Mössbauer spectroscopy with a $^{57}\text{Co}/\text{Rh}$ source (of approximately 20 mCi of activity) was performed at 300 K in order to char-
407 acterize the iron in the samples using the conversion electron mode. The films were first metallized with a thin layer of aluminum
408 ($\sim 30\text{--}40 \text{ nm}$) to provide a good Ohmic contact and subsequently inserted into the cathode structure of a He-CH_4 filled (5% at 1.7
409 bar) gas-flow proportional counter, for measurements lasting approximately one week in each case. Energy filtering enabled Möss-
410 bauer spectra were acquired for the film (deep electrons and x-rays) and primarily from the surface ($\sim 20\text{--}30 \text{ nm}$ penetration depth,
411 due to Auger electrons) for the sample on STO. No Mössbauer signal could be resolved for the lowest escape energies. The sample
412 on Si had a weaker signal and no energy filtering was performed so the data corresponded to the full thickness. The spectra were
413 fitted using the standard least-squares method, using a pure Fe metal foil for velocity calibration.

414 415 APPENDIX E: THEORETICAL METHOD

416 We performed spin-polarized DFT calculations with a Heyd-Scuseria-Ernzerhof (HSE) functional [86,87] as implemented in the
417 Vienna Ab initio Simulation Package (VASP) and within a PAW-PBE framework [88]. Compared to semi-local DFT methods,
418 HSE improves the accuracy of standard local magnetic moments as well as features of interest such as valence spin states, band-
419 gaps, and lattice parameters, as shown previously for SrCoO_3 and SrTiCoO_3 [83]. A $2\times 2\times 2$ perovskite supercell with 39 or 40 at-
420 oms for $\delta = 0$ or 0.125, respectively, was used. Monkhorst k -point meshes of $2\times 2\times 2$ and $4\times 4\times 4$ were used for relaxation and static
421 calculations, respectively. The energy cutoff used was 500 eV, and forces were converged to within $10^{-5} \text{ eV \AA}^{-1}$.

422 We explored all possible FM and AFM initializations in both high and low spin configurations for different combinations of va-
423 lence states for Fe, i.e., 4 and $0\mu_B$ (high and low spin Fe^{2+}), 5 and $1\mu_B$ (high and low spin Fe^{3+}), and 4 and $2\mu_B$ (high and low spin
424 Fe^{4+}). We also explored perturbations of $\pm 20\%\mu_B$ for every initialization. In total, a few hundred calculations were performed, and
425 in all cases, the magnetic moments were allowed to fully relax to their final value. Some cases with $4 \times 4 \times 4$ supercells were also
426 examined with $x = 0.25$ and $\delta = 0.125$, of which a few reached convergence within a reasonable time. These configurations showed
427 antiferromagnetic coupling between the Fe moments and agreed with the $2\times 2\times 2$ supercell results.

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